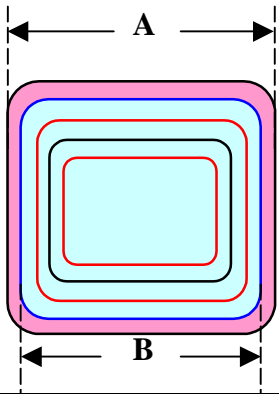


<b>Features :</b>  <ul style="list-style-type: none"> <li>* Extremely low forward volts</li> <li>* Guard ring protection</li> <li>* Low reverse leakage current</li> </ul> 	Chip size(A):	1.016 * 1.016 mm <sup>2</sup>		
	Bond Pad size(B) :	0.889 * 0.889 mm <sup>2</sup>		
	Thickness :	300μm ± 20μm		
	Metalization :	Anode Ti/Ni/Ag		
	Metalization :	Cathode Ti/Ni/Ag		
<b>Electrical Characteristics</b>	Sym.	Spec. Limit	Unit	
Maximum Instantaneous Forward Volt at IF : 1.0Amp. 25°C	VF max	0.43	Volt	
Minimum Instantaneous Reverse Voltage at IR : 200 uA 25°C	VR min.	23	Volt.	
Minimum Non-repetitive Peak Surge current at 25°C	IFSM	40	Amp	
Storage Temperature	TSTG	-65 to +125	°C	

**HsinChu Headquarter**

5F, No. 11, Park Avenue II,  
Science-Based Industrial Park,  
HsinChu City, Taiwan  
TEL: +886-3-567 9979  
FAX: +886-3-567 9909

**Sales & Marketing**

11F, No. 306-3, SEC. 1, Ta Tung Road,  
Hsichih, Taipei Hsien 221, Taiwan  
TEL: +886-2-8692 1591  
FAX: +886-2-8692 1596